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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

ackage / Case	64-LQFP Exposed Pad PG-LQFP-64-6
ounting Type	Surface Mount
perating Temperature	-40°C ~ 85°C (TA)
Scillator Type	Internal
Oata Converters	A/D 9x10b
oltage - Supply (Vcc/Vdd)	3V ~ 5.5V
AM Size	42K x 8
EPROM Size	-
rogram Memory Type	FLASH
rogram Memory Size	320KB (320K x 8)
umber of I/O	38
eripherals	I ² S, POR, PWM, WDT
onnectivity	CANbus, EBI/EMI, I ² C, LINbus, SPI, SSC, UART/USART, USI
peed	66MHz
ore Size	16/32-Bit
Core Processor	C166SV2
roduct Status	Obsolete



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General Device Information

Table 6 Pin Definitions and Functions (cont'd)

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Pin	Symbol	Ctrl.	Type	Function					
31	P2.6	O0 / I	St/B	Bit 6 of Port 2, General Purpose Input/Output					
	U0C0_SELO 0	01	St/B	USIC0 Channel 0 Select/Control 0 Output					
	U0C1_SELO 1	O2	St/B	USIC0 Channel 1 Select/Control 1 Output					
	CC2_CC19	O3 / I	St/B	CAPCOM2 CC19IO Capture Inp./ Compare Out.					
	U0C0_DX2D	I	St/B	USIC0 Channel 0 Shift Control Input					
	RxDC0D	I	St/B	CAN Node 0 Receive Data Input					
	ESR2_6	I	St/B	ESR2 Trigger Input 6					
35	P2.7	O0 / I	St/B	Bit 7 of Port 2, General Purpose Input/Output					
	U0C1_SELO 0	01	St/B	USIC0 Channel 1 Select/Control 0 Output					
	U0C0_SELO 1	O2	St/B	USIC0 Channel 0 Select/Control 1 Output					
	CC2_CC20	O3 / I	St/B	CAPCOM2 CC20IO Capture Inp./ Compare Out.					
	U0C1_DX2C	I	St/B	USIC0 Channel 1 Shift Control Input					
	RxDC1C	I	St/B	CAN Node 1 Receive Data Input					
	ESR2_7	I	St/B	ESR2 Trigger Input 7					
36	P2.8	O0 / I	DP/B	Bit 8 of Port 2, General Purpose Input/Output					
	U0C1_SCLK OUT	01	DP/B	USIC0 Channel 1 Shift Clock Output					
	EXTCLK	O2	DP/B	Programmable Clock Signal Output					
	CC2_CC21	O3 / I	DP/B	CAPCOM2 CC21IO Capture Inp./ Compare Out.					
	U0C1_DX1D	I	DP/B	USIC0 Channel 1 Shift Clock Input					
	+			•					



General Device Information

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
51	P10.8	O0 / I	St/B	Bit 8 of Port 10, General Purpose Input/Output
	U0C0_MCLK OUT	O1	St/B	USIC0 Channel 0 Master Clock Output
	U0C1_SELO 0	O2	St/B	USIC0 Channel 1 Select/Control 0 Output
	U2C1_DOUT	О3	St/B	USIC2 Channel 1 Shift Data Output
	CCU60_CCP OS1A	I	St/B	CCU60 Position Input 1
	U0C0_DX1C	I	St/B	USIC0 Channel 0 Shift Clock Input
	BRKIN_B	I	St/B	OCDS Break Signal Input
	T3EUDB	I	St/B	GPT12E Timer T3 External Up/Down Control Input
52	P10.9	O0 / I	St/B	Bit 9 of Port 10, General Purpose Input/Output
	U0C0_SELO 4	01	St/B	USIC0 Channel 0 Select/Control 4 Output
	U0C1_MCLK OUT	O2	St/B	USIC0 Channel 1 Master Clock Output
	CCU60_CCP OS2A	I	St/B	CCU60 Position Input 2
	TCK_B	IH	St/B	DAP0/JTAG Clock Input If JTAG pos. B is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it. If DAP pos. 1 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.
	T3INB	I	St/B	GPT12E Timer T3 Count/Gate Input
				•

Functional Description

3 Functional Description

The architecture of the XC223xN combines advantages of RISC, CISC, and DSP processors with an advanced peripheral subsystem in a well-balanced design. On-chip memory blocks allow the design of compact systems-on-silicon with maximum performance suited for computing, control, and communication.

The on-chip memory blocks (program code memory and SRAM, dual-port RAM, data SRAM) and the generic peripherals are connected to the CPU by separate high-speed buses. Another bus, the LXBus, connects additional on-chip resources and external resources. This bus structure enhances overall system performance by enabling the concurrent operation of several subsystems of the XC223xN.

The block diagram gives an overview of the on-chip components and the advanced internal bus structure of the XC223xN.

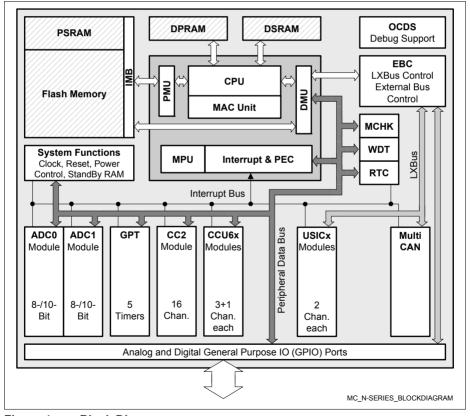


Figure 4 Block Diagram



Functional Description

Memory Content Protection

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).

The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.

The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.



Functional Description

to a dedicated vector table location). The occurrence of a hardware trap is also indicated by a single bit in the trap flag register (TFR). Unless another higher-priority trap service is in progress, a hardware trap will interrupt any ongoing program execution. In turn, hardware trap services can normally not be interrupted by standard or PEC interrupts.

Depending on the package option up to 3 External Service Request (ESR) pins are provided. The ESR unit processes their input values and allows to implement user controlled trap functions (System Requests SR0 and SR1). In this way reset, wakeup and power control can be efficiently realized.

Software interrupts are supported by the 'TRAP' instruction in combination with an individual trap (interrupt) number. Alternatively to emulate an interrupt by software a program can trigger interrupt requests by writing the Interrupt Request (IR) bit of an interrupt control register.

3.6 On-Chip Debug Support (OCDS)

The On-Chip Debug Support system built into the XC223xN provides a broad range of debug and emulation features. User software running on the XC223xN can be debugged within the target system environment.

The OCDS is controlled by an external debugging device via the debug interface. This either consists of the 2-pin Device Access Port (DAP) or of the JTAG port conforming to IEEE-1149. The debug interface can be completed with an optional break interface.

The debugger controls the OCDS with a set of dedicated registers accessible via the debug interface (DAP or JTAG). In addition the OCDS system can be controlled by the CPU, e.g. by a monitor program. An injection interface allows the execution of OCDS-generated instructions by the CPU.

Multiple breakpoints can be triggered by on-chip hardware, by software, or by an external trigger input. Single stepping is supported, as is the injection of arbitrary instructions and read/write access to the complete internal address space. A breakpoint trigger can be answered with a CPU halt, a monitor call, a data transfer, or/and the activation of an external signal.

Tracing of data can be obtained via the debug interface, or via the external bus interface for increased performance.

Tracing of program execution is supported by the XC2000 Family emulation device. With this device the DAP can operate on clock rates of up to 20 MHz.

The DAP interface uses two interface signals, the JTAG interface uses four interface signals, to communicate with external circuitry. The debug interface can be amended with two optional break lines.



Functional Description

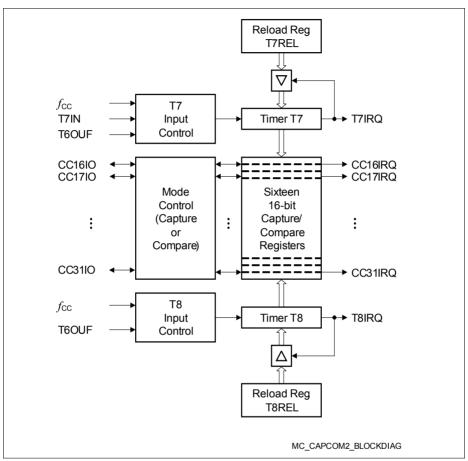


Figure 6 CAPCOM Unit Block Diagram



Functional Description

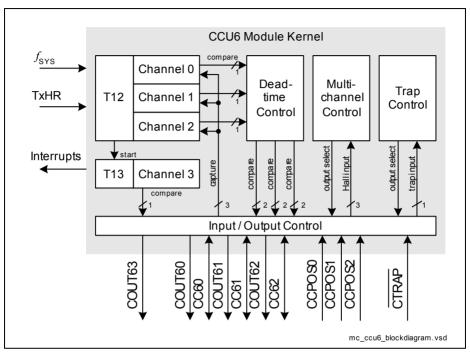


Figure 7 CCU6 Block Diagram

Timer T12 can work in capture and/or compare mode for its three channels. The modes can also be combined. Timer T13 can work in compare mode only. The multi-channel control unit generates output patterns that can be modulated by timer T12 and/or timer T13. The modulation sources can be selected and combined for signal modulation.



Functional Description

3.13 MultiCAN Module

The MultiCAN module contains independently operating CAN nodes with Full-CAN functionality which are able to exchange Data and Remote Frames using a gateway function. Transmission and reception of CAN frames is handled in accordance with CAN specification V2.0 B (active). Each CAN node can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers.

All CAN nodes share a common set of message objects. Each message object can be individually allocated to one of the CAN nodes. Besides serving as a storage container for incoming and outgoing frames, message objects can be combined to build gateways between the CAN nodes or to set up a FIFO buffer.

Note: The number of CAN nodes and message objects depends on the selected device type.

The message objects are organized in double-chained linked lists, where each CAN node has its own list of message objects. A CAN node stores frames only into message objects that are allocated to its own message object list and it transmits only messages belonging to this message object list. A powerful, command-driven list controller performs all message object list operations.

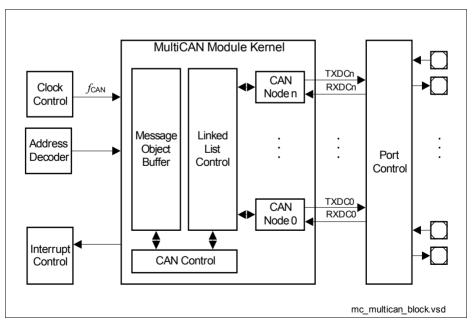


Figure 12 Block Diagram of MultiCAN Module



Functional Description

Table 11 Instruction Set Summary (cont'd)

Mnemonic	Description	Bytes
ROL/ROR	Rotate left/right direct word GPR	2
ASHR	Arithmetic (sign bit) shift right direct word GPR	2
MOV(B)	Move word (byte) data	2/4
MOVBS/Z	Move byte operand to word op. with sign/zero extension	2/4
JMPA/I/R	Jump absolute/indirect/relative if condition is met	4
JMPS	Jump absolute to a code segment	4
JB(C)	Jump relative if direct bit is set (and clear bit)	4
JNB(S)	Jump relative if direct bit is not set (and set bit)	4
CALLA/I/R	Call absolute/indirect/relative subroutine if condition is met	4
CALLS	Call absolute subroutine in any code segment	4
PCALL	Push direct word register onto system stack and call absolute subroutine	4
TRAP	Call interrupt service routine via immediate trap number	2
PUSH/POP	Push/pop direct word register onto/from system stack	2
SCXT	Push direct word register onto system stack and update register with word operand	4
RET(P)	Return from intra-segment subroutine (and pop direct word register from system stack)	2
RETS	Return from inter-segment subroutine	2
RETI	Return from interrupt service subroutine	2
SBRK	Software Break	2
SRST	Software Reset	4
IDLE	Enter Idle Mode	4
PWRDN	Unused instruction ¹⁾	4
SRVWDT	Service Watchdog Timer	4
DISWDT/ENWDT	Disable/Enable Watchdog Timer	4
EINIT	End-of-Initialization Register Lock	4
ATOMIC	Begin ATOMIC sequence	2
EXTR	Begin EXTended Register sequence	2
EXTP(R)	Begin EXTended Page (and Register) sequence	2/4
EXTS(R)	Begin EXTended Segment (and Register) sequence	2/4



Electrical Parameters

4 Electrical Parameters

The operating range for the XC223xN is defined by its electrical parameters. For proper operation the specified limits must be respected when integrating the device in its target environment.

4.1 General Parameters

These parameters are valid for all subsequent descriptions, unless otherwise noted.

Table 12 Absolute Maximum Rating Parameters

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Output current on a pin when high value is driven	$I_{OH}SR$	-30	-	-	mA	
Output current on a pin when low value is driven	$I_{\rm OL}{\rm SR}$	-	-	30	mA	
Overload current	$I_{OV}SR$	-10	_	10	mA	1)
Absolute sum of overload currents	$\Sigma I_{OV} $ SR	_	_	100	mA	1)
Junction Temperature	$T_{J}SR$	-40	_	150	°C	
Storage Temperature	$T_{\rm ST}{\rm SR}$	-65	_	150	°C	
Digital supply voltage for IO pads and voltage regulators	$V_{DDP}SR$	-0.5	-	6.0	V	
Voltage on any pin with respect to ground (Vss)	$V_{IN}SR$	-0.5	-	<i>V</i> _{DDP} + 0.5	V	$V_{IN} \leq V_{DDP(max)}$

Overload condition occurs if the input voltage V_{IN} is out of the absolute maximum rating range. In this case the current must be limited to the listed values by design measures.

Note: Stresses above the values listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for an extended time may affect device reliability. During absolute maximum rating overload conditions ($V_{\rm IN} > V_{\rm DDP}$ or $V_{\rm IN} < V_{\rm SS}$) the voltage on $V_{\rm DDP}$ pins with respect to ground ($V_{\rm SS}$) must not exceed the values defined by the absolute maximum ratings.



Electrical Parameters

- 7) An overload current (I_{OV}) through a pin injects a certain error current (I_{INJ}) into the adjacent pins. This error current adds to the respective pins leakage current (I_{OZ}) . The amount of error current depends on the overload current and is defined by the overload coupling factor K_{OV} . The polarity of the injected error current is inverse compared to the polarity of the overload current that produces it. The total current through a pin is $|I_{\text{TOT}}| = |I_{\text{OZ}}| + (|I_{\text{OV}}| K_{\text{OV}})$. The additional error current may distort the input voltage on analog inputs.
- 8) Value is controlled by on-chip regulator

4.2 Voltage Range definitions

The XC223xN timing depends on the supply voltage. If such a dependency exists the timing values are given for 2 voltage areas commonly used. The voltage areas are defined in the following tables.

Table 14 Upper Voltage Range Definition

Parameter	Symbol		Values		Unit	Note / Test Condition
		Min.	Typ.	Max.		
Digital supply voltage for IO pads and voltage regulators	$V_{DDP}SR$	4.5	5	5.5	V	

Table 15 Lower Voltage Range Definition

Parameter	Symbol	ol Values		Unit		Note /
		Min.	Тур.	Max.		Test Condition
Digital supply voltage for IO pads and voltage regulators	$V_{DDP}SR$	3.0	3.3	4.5	V	

4.2.1 Parameter Interpretation

The parameters listed in the following include both the characteristics of the XC223xN and its demands on the system. To aid in correctly interpreting the parameters when evaluating them for a design, they are marked accordingly in the column "Symbol":

CC (Controller Characteristics):

The logic of the XC223xN provides signals with the specified characteristics.

SR (System Requirement):

The external system must provide signals with the specified characteristics to the XC223xN.



Electrical Parameters

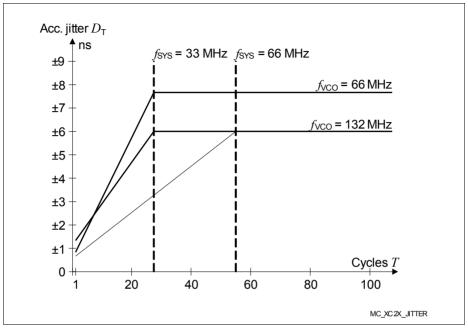


Figure 20 Approximated Accumulated PLL Jitter

Note: The specified PLL jitter values are valid if the capacitive load per pin does not exceed C_1 = 20 pF.

The maximum peak-to-peak noise on the pad supply voltage (measured between $V_{\rm DDPB}$ pin 64 and $V_{\rm SS}$ pin 1) is limited to a peak-to-peak voltage of $V_{\rm PP}$ = 50 mV. This can be achieved by appropriate blocking of the supply voltage as close as possible to the supply pins and using PCB supply and ground planes.

PLL frequency band selection

Different frequency bands can be selected for the VCO so that the operation of the PLL can be adjusted to a wide range of input and output frequencies:



Electrical Parameters

Table 26 System PLL Parameters

Parameter	Symbol		Values	s	Unit	Note /
		Min.	Тур.	Max.		Test Condition
VCO output frequency	$f_{ m VCO}$ CC	50	-	110	MHz	VCOSEL= 00b; VCOmode= controlled
		10	_	40	MHz	VCOSEL= 00b; VCOmode= free running
		100	-	160	MHz	VCOSEL= 01b; VCOmode= controlled
		20	-	80	MHz	VCOSEL= 01b; VCOmode= free running

4.7.2.2 Wakeup Clock

When wakeup operation is selected (SYSCON0.CLKSEL = 00_B), the system clock is derived from the low-frequency wakeup clock source:

$$f_{SYS} = f_{WU}$$
.

In this mode, a basic functionality can be maintained without requiring an external clock source and while minimizing the power consumption.

4.7.2.3 Selecting and Changing the Operating Frequency

When selecting a clock source and the clock generation method, the required parameters must be carefully written to the respective bit fields, to avoid unintended intermediate states.

Many applications change the frequency of the system clock (f_{SYS}) during operation in order to optimize system performance and power consumption. Changing the operating frequency also changes the switching currents, which influences the power supply.

To ensure proper operation of the on-chip EVRs while they generate the core voltage, the operating frequency shall only be changed in certain steps. This prevents overshoots and undershoots of the supply voltage.

To avoid the indicated problems, recommended sequences are provided which ensure the intended operation of the clock system interacting with the power system. Please refer to the Programmer's Guide.



Electrical Parameters

4.7.3 External Clock Input Parameters

These parameters specify the external clock generation for the XC223xN. The clock can be generated in two ways:

- By connecting a crystal or ceramic resonator to pins XTAL1/XTAL2.
- By supplying an external clock signal
 - This clock signal can be supplied either to pin XTAL1 (core voltage domain) or to pin CLKIN1 (IO voltage domain).

If connected to CLKIN1, the input signal must reach the defined input levels $V_{\rm IL}$ and $V_{\rm IH}$. If connected to XTAL1, a minimum amplitude $V_{\rm AX1}$ (peak-to-peak voltage) is sufficient for the operation of the on-chip oscillator.

Note: The given clock timing parameters $(t_1 \dots t_4)$ are only valid for an external clock input signal.

Note: Operating Conditions apply.

Table 27 External Clock Input Characteristics

Parameter	Symbol		Values	3	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Oscillator frequency	$f_{\rm OSC}{\rm SR}$	4	_	40	MHz	Input= Clock Signal
		4	-	16	MHz	Input= Crystal or Ceramic Resonator
XTAL1 input current absolute value	I _{IL} CC	_	_	20	μА	
Input clock high time	t ₁ SR	6	-	_	ns	
Input clock low time	t_2 SR	6	-	_	ns	
Input clock rise time	t_3 SR	_	8	8	ns	
Input clock fall time	t_4 SR	_	8	8	ns	
Input voltage amplitude on XTAL1 ¹⁾	$V_{AX1}SR$	$V_{\rm DDIM}$	_	_	V	$f_{\rm OSC}{\ge}$ 4 MHz; $f_{\rm OSC}{<}$ 16 MHz
		$V_{\rm DDIM}$	_	_	V	$f_{\rm OSC}{\geq}$ 16 MHz; $f_{\rm OSC}{<}$ 25 MHz
		$V_{\rm DDIM}$	_	_	V	$f_{\rm OSC} \ge 25 \ { m MHz};$ $f_{ m OSC} \le 40 \ { m MHz}$
Input voltage range limits for signal on XTAL1	$V_{\rm IX1}$ SR	-1.7 + V _{DDIM}	_	1.7	V	2)



Electrical Parameters

Table 28 Standard Pad Parameters for Upper Voltage Range (cont'd)

Parameter	Symbol		Values		Unit	Note /			
		Min.	Тур.	Max.		Test Condition			
Rise and Fall times (10% - 90%)	t _{RF} CC	_	_	23 + 0.6 x C _L	ns	$C_{\rm L} \ge$ 20 pF; $C_{\rm L} \le$ 100 pF; Driver_Strength = Medium			
		_	_	11.6 + 0.22 x C _L	ns	$\begin{split} &C_{\text{L}}{\geq}\ 20\ \text{pF};\\ &C_{\text{L}}{\leq}\ 100\ \text{pF};\\ &\text{Driver_Strength}\\ &=\ \text{Strong}\ ;\\ &\text{Driver_Edge=}\\ &\text{Medium} \end{split}$			
			_	-	4.2 + 0.14 x C_{L}	ns	$C_{\text{L}} \ge 20 \text{ pF};$ $C_{\text{L}} \le 100 \text{ pF};$ Driver_Strength = Strong; Driver_Edge= Sharp		
						_	-	20.6 + 0.22 x C_{L}	ns
		_	_	212 + 1.9 x C_{L}	ns	$C_{\rm L} \ge 20~{\rm pF};$ $C_{\rm L} \le 100~{\rm pF};$ Driver_Strength = Weak			

An output current above |I_{OXnom}| may be drawn from up to three pins at the same time. For any group of 16 neighboring output pins, the total output current in each direction (\(\Sigma I_{OL}\) and \(\Sigma - I_{OH}\)) must remain below 50 mA.



Electrical Parameters

4.7.5 Synchronous Serial Interface Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 30 is valid under the following conditions: C_L = 20 pF; SSC= master; voltage range= upper

Table 30 USIC SSC Master Mode Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Slave select output SELO active to first SCLKOUT transmit edge	t ₁ CC	<i>t</i> _{SYS} - 8 ¹⁾	-	_	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t ₂ CC	<i>t</i> _{SYS} - 6 ¹⁾	-	-	ns	
Data output DOUT valid time	t ₃ CC	-6	-	9	ns	
Receive data input setup time to SCLKOUT receive edge	t ₄ SR	31	-	-	ns	
Data input DX0 hold time from SCLKOUT receive edge	t ₅ SR	-4	-	-	ns	

¹⁾ $t_{SYS} = 1 / f_{SYS}$

Table 31 is valid under the following conditions: C_L = 20 pF; SSC= master; voltage_range= lower

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Electrical Parameters

Table 37 JTAG Interface Timing for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
TDI/TMS hold after TCK rising edge	t ₇ SR	6	_	_	ns	
TDO valid from TCK falling edge (propagation delay) ¹⁾	t ₈ CC	_	32	36	ns	
TDO high impedance to valid output from TCK falling edge ²⁾¹⁾	t ₉ CC	-	32	36	ns	
TDO valid output to high impedance from TCK falling edge ¹⁾	t ₁₀ CC	-	32	36	ns	
TDO hold after TCK falling edge ¹⁾	t ₁₈ CC	5	-	_	ns	

¹⁾ The falling edge on TCK is used to generate the TDO timing.

²⁾ The setup time for TDO is given implicitly by the TCK cycle time.

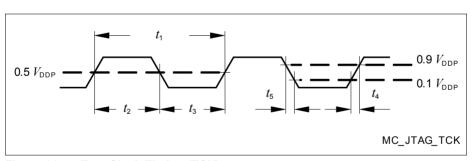


Figure 26 Test Clock Timing (TCK)

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Package and Reliability

5.2 Thermal Considerations

When operating the XC223xN in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The "Thermal resistance $R_{\rm \odot JA}$ " quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 150 °C.

The difference between junction temperature and ambient temperature is determined by $\Delta T = (P_{\text{INT}} + P_{\text{IOSTAT}} + P_{\text{IODYN}}) \times R_{\Theta,\text{IA}}$

The internal power consumption is defined as

 $P_{\mathsf{INT}} = V_{\mathsf{DDP}} \times I_{\mathsf{DDP}}$ (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as $P_{\text{IOSTAT}} = \Sigma((V_{\text{DDP}} - V_{\text{OH}}) \times I_{\text{OH}}) + \Sigma(V_{\text{OL}} \times I_{\text{OL}})$

The dynamic external power consumption caused by the output drivers (P_{IODYN}) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce V_{DDP} , if possible in the system
- Reduce the system frequency
- · Reduce the number of output pins
- Reduce the load on active output drivers



Package and Reliability

5.3 Quality Declarations

The operation lifetime of the XC223xN depends on the applied temperature profile in the application. For a typical example, please refer to **Table 40**; for other profiles, please contact your Infineon counterpart to calculate the specific lifetime within your application.

Table 39 Quality Parameters

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Operation lifetime	t _{OP} CC	-	-	20	а	See Table 40 and Table 41
ESD susceptibility according to Human Body Model (HBM)	V _{HBM} SR	-	_	2 000	V	EIA/JESD22- A114-B
Moisture sensitivity level	MSL CC	-	_	3	_	JEDEC J-STD-020C

Table 40 Typical Usage Temperature Profile

Operating Time (Sum = 20 years)	Operating Temperat.	Notes
1 200 h	T _J = 150°C	Normal operation
3 600 h	T _J = 125°C	Normal operation
7 200 h	T _J = 110°C	Normal operation
12 000 h	T _J = 100°C	Normal operation
7 × 21 600 h	$T_{\rm J}$ = 010°C,, 6070°C	Power reduction

Table 41 Long Time Storage Temperature Profile

Operating Time (Sum = 20 years)	Operating Temperat.	Notes	
2 000 h	T _J = 150°C	Normal operation	
16 000 h	T _J = 125°C	Normal operation	
6 000 h	$T_{\rm J}$ = 110°C	Normal operation	
151 200 h	<i>T</i> _J ≤ 150°C	No operation	